TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

T C 7 M H 2 3 8 F K

3-to-8 Line Decoder

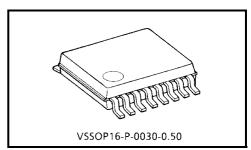
The TC7MH238FK is an advanced high speed CMOS 3-to-8 decoder fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

When the device is enabled, 3 binary select inputs (A, B and C) determine which one of the outputs (Y0-Y7) will go high.

When enable input G1 is held low or either $\overline{G}2A$ or $\overline{G}2B$ is held high, decoding function is inhibited and all outputs go low.

G1, G2A and G2B inputs are provided to ease cascade connection and for use as an address decoder for memory systems.



Weight: 0.02 g (typ.)

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High speed: $t_{pd} = 5.5 \text{ ns (typ.) (VCC} = 5 \text{ V)}$
- Low power dissipation: $ICC = 4 \mu A \text{ (max)} \text{ (Ta} = 25 \text{°C)}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: t_pLH ≃ t_pHL
- Wide operating voltage range: V_{CC} (opr) = 2~5.5 V
- Pin and function compatible with 74ALS238

000630EBA²

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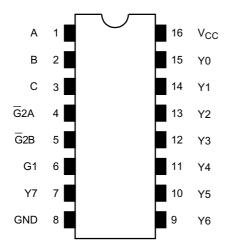
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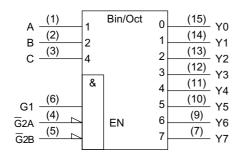
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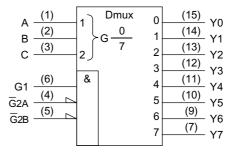


Pin Assignment (top view)



IEC Logic Symbol





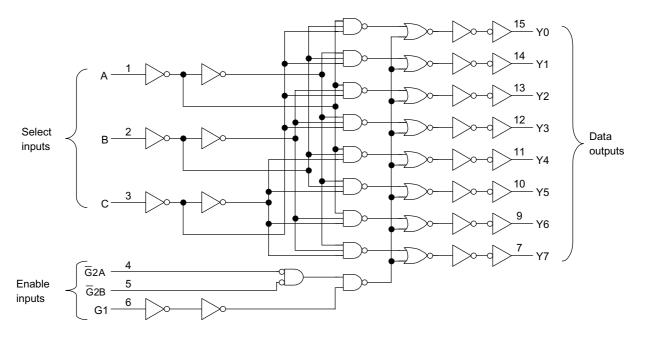
Truth Table

Inputs					Outputs												
	Enable			Select			Y1	Y2	Y3	Y4	Y5	Y6	Y7	Selected Output			
G1	G ₂ A	G ₂ B	С	В	Α	Y0	1 !	12	13	14	13	10	17				
L	Х	Х	Х	Х	Х	L	L	L	L	L	L	L	L	None			
Х	Н	Х	X	X	X	L	L	L	L	L	L	لــ	لــ	None			
Х	Х	Η	X	X	X	L	L	L	L	L	L	لــ	لــ	None			
Н	L	L	Ш	Ш	Ш	Н	L	L	L	L	L	لــ	لــ	Y0			
Н	L	L	Ш	Ш	Ι	L	Н	L	L	L	L	لــ	لــ	Y1			
Н	L	L	Ш	Η	Ш	L	L	Н	L	L	L	لــ	لــ	Y2			
Н	L	L	L	Н	Н	L	L	L	Н	L	L	L	L	Y3			
Н	L	L	Н	L	L	L	L	L	L	Н	L	L	L	Y4			
Н	L	L	Н	L	Н	L	L	L	L	L	Н	L	L	Y5			
Н	L	L	Н	Н	L	L	L	L	L	L	L	Н	L	Y6			
Н	L	L	Н	Н	Н	L	L	L	L	L	L	L	Н	Y7			

X: Don't care



System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	2.0~5.5	V	
Input voltage	V _{IN}	0~5.5	V	
Output voltage	V _{OUT}	0~V _{CC}	V	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	$0\sim100 \ (V_{CC}=3.3\pm0.3 \ V)$	ns/V	
input rise and fair time	αι/αν	0~20 (V _{CC} = 5 ± 0.5 V)	115/V	



Electrical Characteristics

DC Characteristics

Characteristics		Symbol	Test Condition			7	Га = 25°C		Ta = -4	Lloit	
Characte	eristics	Symbol	rest Condition		V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit
Input voltage					2.0	1.50	_	_	1.50	_	V
	High level	V _{IH}			3.0~5.5	$\begin{matrix} V_{CC} \\ \times 0.7 \end{matrix}$	_	_	V _{CC} × 0.7	_	
iliput voltage					2.0	_	_	0.50	_	0.50	V
	Low level	V _{IL}		_	3.0~5.5	_	_	$\begin{array}{c} V_{CC} \\ \times 0.3 \end{array}$	_	$\begin{array}{c} V_{CC} \\ \times 0.3 \end{array}$	
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	2.0	1.9	2.0	_	1.9	_	
					3.0	2.9	3.0	_	2.9	_	
					4.5	4.4	4.5	_	4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
Output voltage				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	V
Output voltage					2.0	_	0	0.1	_	0.1	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1	
					4.5		0	0.1	_	0.1	
				I _{OL} = 4 mA	3.0		_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5		_	0.36	_	0.44	
Input leakage current		I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	_		±0.1	_	±1.0	μΑ
Quiescent supply current		I _{CC}	$V_{IN} = V_{CC}$ or GND		5.5	_	_	4.0	_	40.0	μΑ



AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

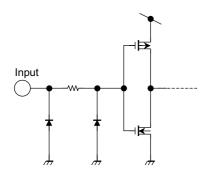
Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -4	Unit	
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Unit
			3.3 ± 0.3	15	_	8.0	12.3	1.0	14.5	ns
Propagation delay time	t _{pLH}			50		10.5	15.8	1.0	18.0	
(A, B, C-Y)	tpHL	_	5.0 ± 0.5	15		5.5	8.1	1.0	9.5	113
		5.	3.0 ± 0.5	50		7.0	10.1	1.0	11.5	
	t _{pLH}	_	3.3 ± 0.3	15		8.1	12.8	1.0	15.0	ns
Propagation delay time				50		10.6	16.3	1.0	18.5	
(G1-Y)	t _{pHL}		5.0 ± 0.5	15		5.4	8.1	1.0	9.5	
				50	_	6.9	10.1	1.0	Max 14.5 18.0 9.5 11.5 15.0 18.5	
	t _{oLH}	_	3.3 ± 0.3	15	_	8.1	12.3	1.0	14.5	
Propagation delay time				50		10.6	15.8	1.0	18.0	
(G 2 -Y)	t _{pLH} t _{pHL}		5.0 ± 0.5	15		5.7	8.1	1.0	9.5	
				50		7.2	10.1	1.0	11.5	
Input capacitance	C _{IN}	-	_		_	4	_	_	10	pF
Power dissipation capacitance	C _{PD}			(Note)	_	37	_			pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

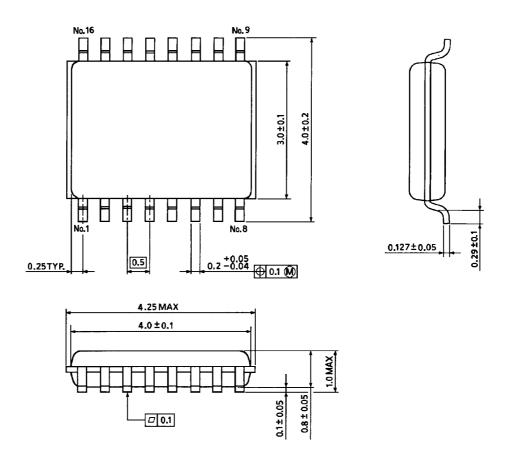
Average operating current can be obtained by the equation:

ICC (opr) = CPD · VCC · fIN + ICC

Input Equivalent Circuit



Package Dimensions



Weight: 0.02 g (typ.)